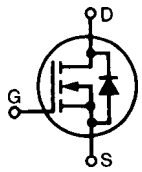
HiPerFET™ Power MOSFETs ISOPLUS247™

(Electrically Isolated Backside)

N-Channel Enhancement Mode
Avalanche Rated, Low Q_g, High dv/dt

IXFR 80N15Q

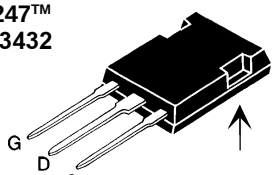
V_{DSS} = 150 V
I_{D25} = 75 A
$R_{DS(on)}$ = 22.5 mΩ
$t_{rr} \leq$ 200ns



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	150	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ	150	V
V_{GS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	75	A
I_{DM}	T_C = 25°C, Note 1	320	A
I_{AR}	T_C = 25°C	80	A
E_{AR}	T_C = 25°C	45	mJ
E_{AS}	T_C = 25°C	1.5	J
dv/dt	$I_S \leq I_{DM}$, di/dt ≤ 100 A/μs, $V_{DD} \leq V_{DSS}$ $T_J \leq$ 150°C, R_G = 2 Ω	5	V/ns
P_D	T_C = 25°C	310	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.063 in.) from case for 10 s	300	°C
V_{ISOL}	50/60 Hz, RMS t = 1 min	2500	V~
Weight		5	g

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
V_{DSS}	V_{GS} = 0 V, I_D = 250μA	150			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 4mA	2.0		4.0	V
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0 V, T_J = 25°C			25	μA
	$V_{DS} = V_{DSS}$, V_{GS} = 0 V, T_J = 125°C			1	mA
$R_{DS(on)}$	V_{GS} = 10 V, $I_D = I_T$ Notes 2, 3			22.5	mΩ

ISOPLUS247™
E153432



Isolated backside*

G = Gate D = Drain
S = Source

* Patent pending

Features

- Silicon chip on Direct-Copper-Bond substrate
  - High power dissipation
  - Isolated mounting surface
  - 2500V electrical isolation
- Low drain to tab capacitance(<30pF)
- Low $R_{DS\ (on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Rated for Unclamped Inductive Load Switching (UIS)
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control

Advantages

- Easy assembly
- Space savings
- High power density

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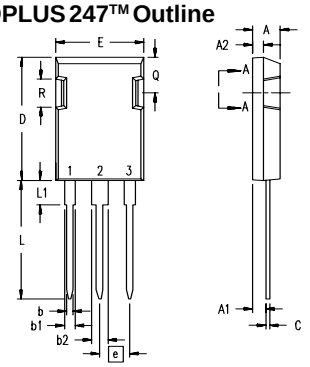
Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	V_{DS} = 10 V; I_D = I_T Notes 2, 3	35	50		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		4600		pF
C_{oss}			1400		pF
C_{rss}			680		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = I_T R_G = 2 Ω (External), Notes 2, 3		30		ns
t_r			55		ns
$t_{d(off)}$			68		ns
t_f			20		ns
$Q_{g(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = I_T Notes 2, 3		180		nC
Q_{gs}			39		nC
Q_{gd}			85		nC
R_{thJC}				0.40	K/W
R_{thCK}			0.15		K/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values min.	typ.	max.	
I_S	V_{GS} = 0 V			80	A
I_{SM}	Repetitive; Note 1			320	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Notes 2, 3			1.5	V
t_{rr}	I_F = 50A,-di/dt = 100 A/μs, V_R = 100 V			200	ns
Q_{RM}			1.2		μC
I_{RM}			10		A

Note: 1. Pulse width limited by T_{JM}
2. Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %
3. I_T = 40A

ISOPLUS 247™ Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.83	5.21	.190	.205
A_1	2.29	2.54	.090	.100
A_2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b_1	1.91	2.13	.075	.084
b_2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025